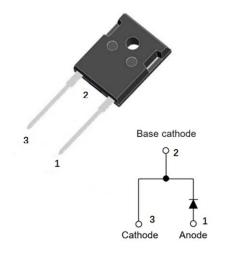


YJD112030NGH

RoHS COMPLIANT

Silicon Carbide Schottky Diode

V _{RRM}	1200V
I _F (135°C)	40A
Q _c	205nC



Features

- Positive temperature coefficient
- Temperature-independent switching
 Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

- Package: TO-247AC Molding compound meets UL 94 V-0 flammability
- rating, RoHS-compliant, halogen-free
- Terminals: Tin plated leads
- Polarity: As marked

■Maximum Ratings (T_c =25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D112030NGH
Reverse voltage (Repetitive peak) @ T _j =25°C	V _{RRM}	V	1200
Reverse voltage (Surge peak) @ T _j =25°C	V _{RSM}	V	1200
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	1200
Continuous forward current @ T _c =25°C	I _F	A	86
Continuous forward current @ T _c =135°C			40
Continuous forward current @ T _c =150°C			30
Non-repetitive peak forward surge current @ T_c =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	261
Power Dissipation@ T _c =25°C	5	w	333
Power Dissipation@ T _c =110°C	P _{TOT}		144
i²t Value@ T _c =25°C ,tp=10ms	∫ i²dt	A ² S	340
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175

1/5



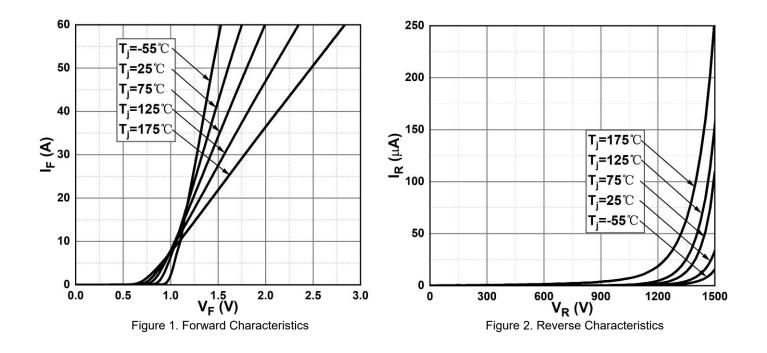
Electrical Characteristics

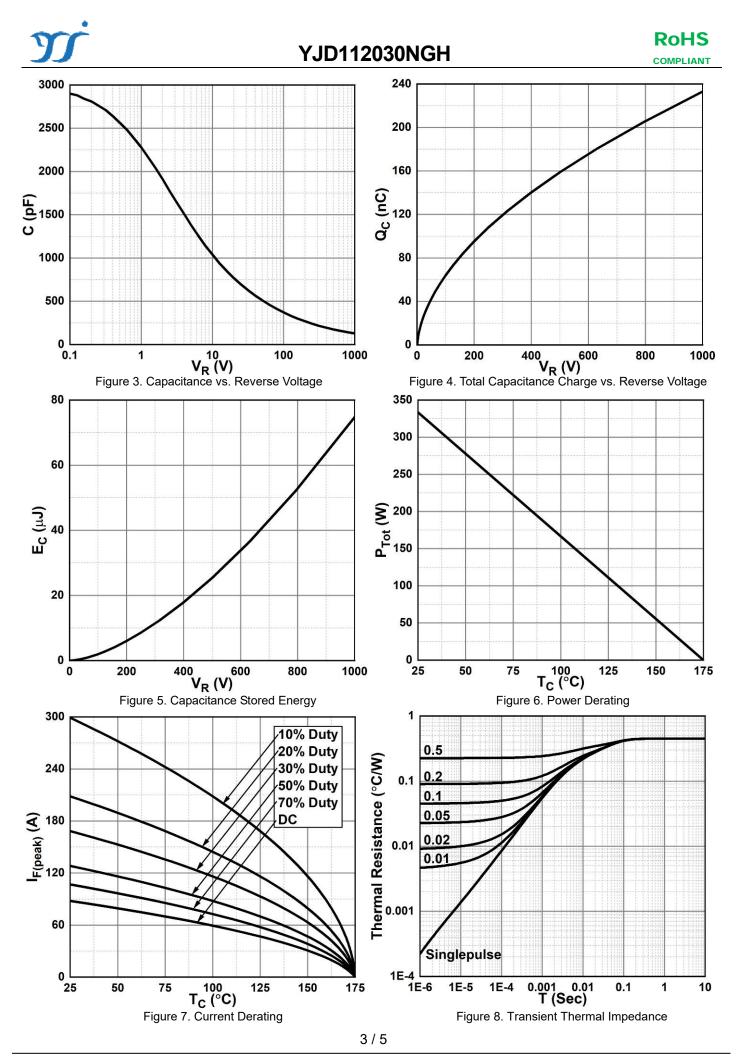
PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drop	VF	V	I _F =30A, T _j =25°C	1.38	1.55
			I _F =30A, T _j =175°C	1.8	-
	I _R	μA	V _R =1200V, T _j =25°C	1	20
Reverse leakage current			V _R =1200V, T _j =175°C	19	-
Total capacitive charge	Qc	nC	V_R =800V, T _j =25°C , Q_C = $\int_0^{VR} C(V) dV$	205	-
	C pF	pF	V _R =0V, f=1MHZ	2902	-
Total capacitance			V _R =400V, f=1MHZ	194	-
			V _R =800V, f=1MHZ	143	-
Capacitance Stored Energy	Ec	μJ	V _R =800V	53	-

■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{_{ ext{ hetaJ-C}}}$	°C /W	0.45

■Typical Characteristics



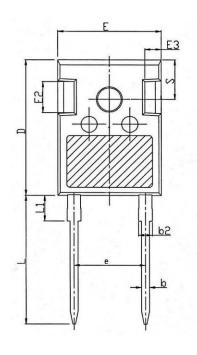


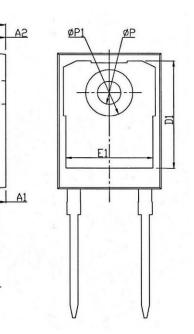
Yangzhou Yangjie Electronic Technology Co., Ltd.



Outline Dimensions

TO-247AC





TO-247AC					
Min	Max				
4.80	5.20				
2.21	2.61				
1.85	2.15				
1.11	1.36				
1.91	2.21				
0.51	0.75				
20.70	21.30				
16.25	16.85				
15.50	16.10				
13.00	13.60				
4.80	5.20				
2.30	2.70				
10.88BSC					
19.62	20.22				
-	4.30				
3.40	3.80				
-	7.30				
6.15BSC					
	Min 4.80 2.21 1.85 1.11 1.91 0.51 20.70 16.25 15.50 13.00 4.80 2.30 10.88 19.62 - 3.40 -				



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